

SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

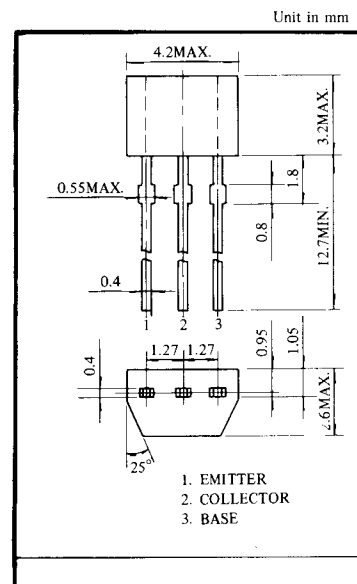
2SA1272

APPLICATION

- Low Frequency Amplifier Applications.

FEATURES

- High h_{FE} : $h_{FE}=100\sim320$.
- Complementary to 2SC3204.



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V	Emitter Current	I_E	800	mA
Collector-Emitter Voltage	V_{CEO}	-30	V	Collector Power Dissipation	P_C	300	mW
Emitter-Base Voltage	V_{EBO}	-5	V	Junction Temperature	T_J	125	°C
Collector Current	I_C	-800	mA	Storage Temperature Range	T_{stg}	-55~125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30V, I_E=0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA$	-30	—	—	V
Dc Current Gain	$h_{FE(1)}/NOTE$	$V_{CE}=-1V, I_C=-100mA$	100	—	320	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-700mA$	35	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$	—	—	-0.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5	—	-0.8	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-10mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz$	—	19	—	pF

NOTE: According to $h_{FE(1)}$, Classified as follows.

0	100~200	Y	160~320
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